REMARKS

Claims 1-5, 7-16 and 35 are pending in this application.

Claim 1 is amended, claim 35 is canceled, and claim 36 is added by the present amendment. No new matter is added in the amendment.

Applicants request reconsideration of the pending claims in light of the above claim amendment taken along with the following remarks.

Claim Rejection under 35 U.S.C. 102

Claims 1-3 and 5 stand rejected under 35 U.S.C. §102(b) as being anticipated by Ogura et al. (U.S. Pat. No. 6,388,293) for reasons recited in pages 2 and 3 of the April 11, 2006 Final Office Action.

Claim 1 recites, inter alia, a gate insulation pattern covering the entire sidewall of a selection gate electrode proximal to a control gate pattern. The claim feature prevents direct contact between the selection gate electrode and the control gate pattern.

Examiner states that <u>Ogura</u> discloses a gate insulation pattern (401/402/103) interposed between a selection gate electrode (241) and a control gate pattern (132). Applicants respectfully submit that the gate insulation pattern (401/402/103) of <u>Ogura</u> does <u>not</u> cover the <u>entire</u> sidewall of the selection gate electrode (241) proximal to the control gate pattern (132). Thus, a portion of the selection gate electrode (241) directly contacts the control gate pattern (132). <u>See</u> Fig. 18.

Claims 2, 3 and 5 depend from claim 1. The dependent claims are allowable for at least the reasons provided for base claim 1.

Accordingly, the Applicants respectfully request that the Examiner withdraw the rejection of claims 1-3 and 5 under 35 U.S.C § 102(b) and that claims 1-3 and 5 are in condition for allowance.

Claims 1-5 and 35 stand rejected under 35 U.S.C. §102(b) as being anticipated by Lung et al. (U.S. Pub. 2002/0145160) for reasons recited in pages 3 and 4 of the April 11, 2006 Final Office Action.

Claim 1 recites, inter alia, a gate insulation pattern interposed between a selection gate electrode and a semiconductor substrate.

Examiner states that <u>Lung</u> discloses a gate insulation pattern (208 and part of 205) interposed between a selection gate (207) and a semiconductor substrate (201). Applicants

respectfully disagree. The component (205) is not a gate insulation pattern, but a carrier trapping dielectric layer. See paragraph [0026]. Contrast to the instant Application where only a portion of the channel region (a) includes a carrier trapping dielectric layer (105a), the carrier trapping dielectric layer (205) of Lung is formed over the entire channel region (204). Accordingly, reducing program voltages applied to the gate cannot be achieved in Lung. Thus, with the component (205) removed as a gate insulation pattern, the gate insulation pattern (208) is not interposed between the selection gate electrode (207) and the semiconductor substrate (201).

Claims 2-5 depend from claim 1. The dependent claims are allowable for at least the reasons provided for base claim 1. Claim 35 has been canceled.

Accordingly, the Applicants respectfully request that the Examiner withdraw the rejection of claims 1-5 under 35 U.S.C § 102(b) and that claims 1-5 are in condition for allowance.

Claim Rejections Under 35 U.S.C. § 103

Claims 8-11 and 14-16 were rejected under 35 U.S.C. § 103(a) as being unpatentable over <u>Lung</u> and in view of U.S. Patent No. 6,785,165 to <u>Kawahara</u>.

For at least the reasons provided above, <u>Lung</u> does not teach or suggest a first gate insulation pattern interposed between a first selection gate electrode and a semiconductor substrate, and a second gate insulation pattern interposed between a second selection gate electrode and the semiconductor substrate, as essentially recited in claim 8.

<u>Kawahara</u> does not cure the deficiency of <u>Lung</u> with regard to the above feature.

Accordingly, claim 8 is patentable over <u>Lung</u> taken with <u>Kawahara</u>. Since claims 9-11 and 14-16 are dependent from claim 8, claims 9-11 and 14-16 are also patentable.

Accordingly, withdrawal of the obviousness rejections is respectfully requested.

Conclusion:

In summary, applicants respectfully submit that the instant application is in condition for allowance. Early notice to that end is earnestly solicited.

If a telephone conference would be of assistance in furthering prosecution of the subject application, applicants request that the undersigned be contacted at the number below.

Respectfully submitted,

Frank Chau

Reg. No. 34,136

Attorney for Applicants

F. Chau & Associates, LLC 130 Woodbury Road Woodbury, NY 11797

Tel: (516) 692-8888 Fax: (516) 692-8889